
2SK1056, 2SK1057, 2SK1058

Silicon N-Channel MOS FET

HITACHI

Application

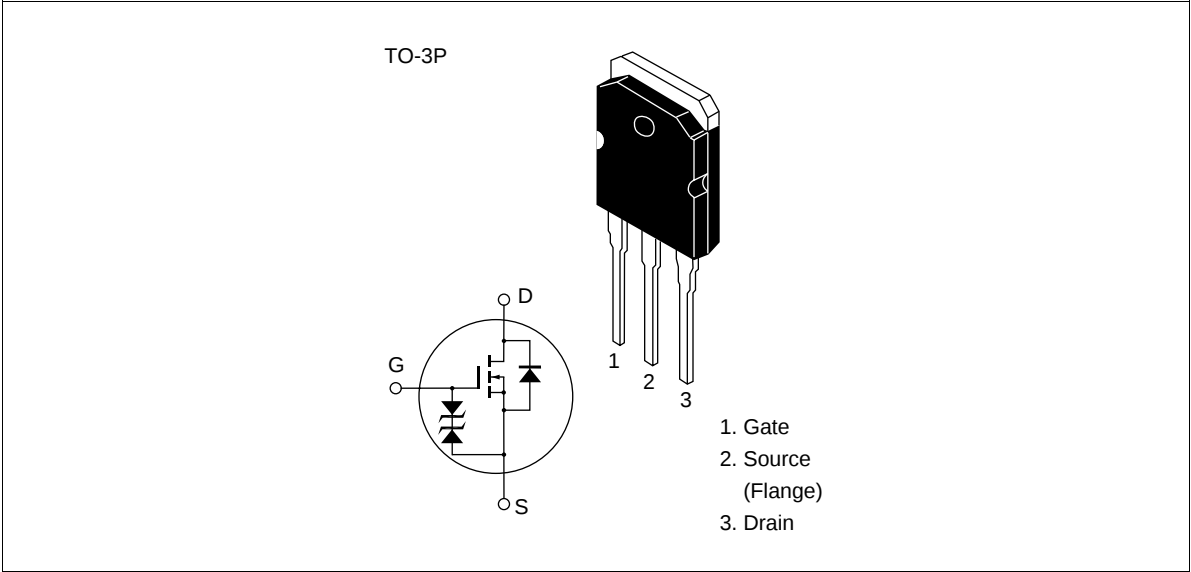
Low frequency power amplifier

Complementary pair with 2SJ160, 2SJ161 and 2SJ162

Features

- Good frequency characteristic
- High speed switching
- Wide area of safe operation
- Enhancement-mode
- Good complementary characteristics
- Equipped with gate protection diodes
- Suitable for audio power amplifier

Outline



Absolute Maximum Ratings (Ta = 25°C)

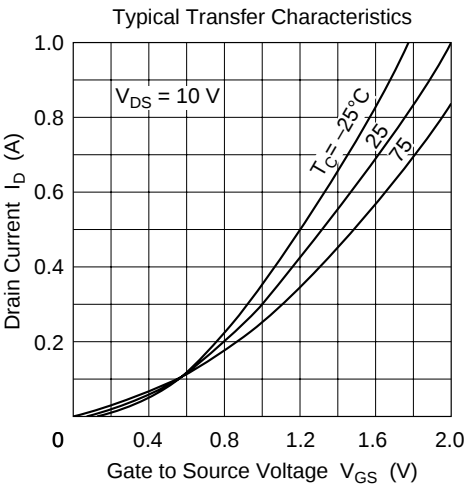
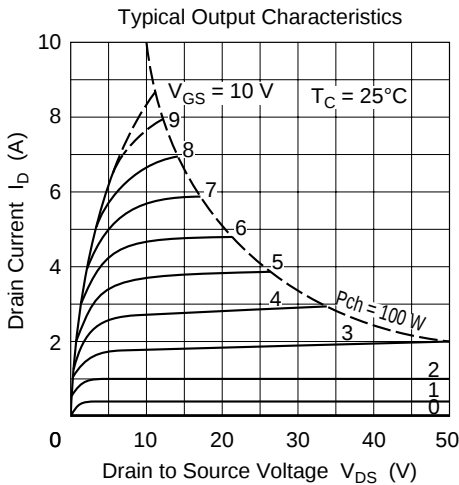
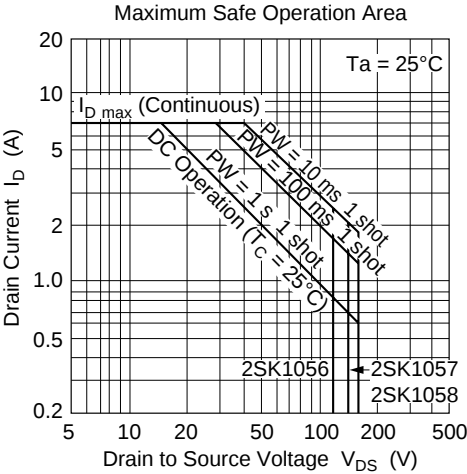
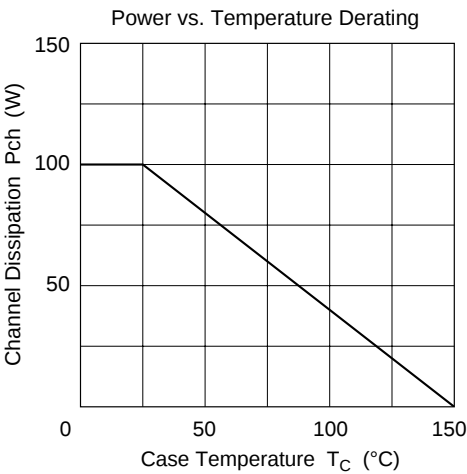
Item		Symbol	Ratings	Unit
Drain to source voltage	2SK1056	V_{DSX}	120	V
	2SK1057		140	
	2SK1058		160	
Gate to source voltage		V_{GSS}	±15	V
Drain current		I_D	7	A
Body to drain diode reverse drain current		I_{DR}	7	A
Channel dissipation		Pch^{*1}	100	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	−55 to +150	°C

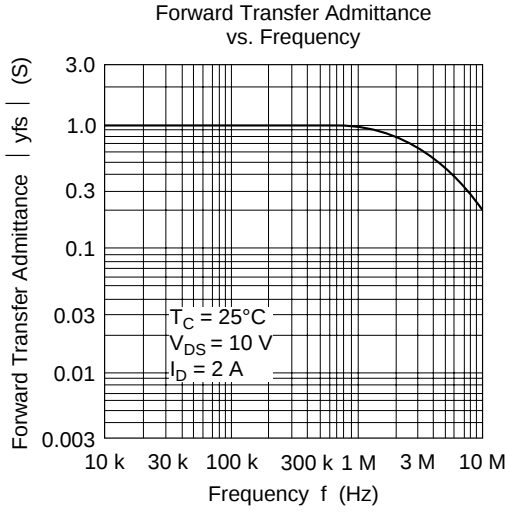
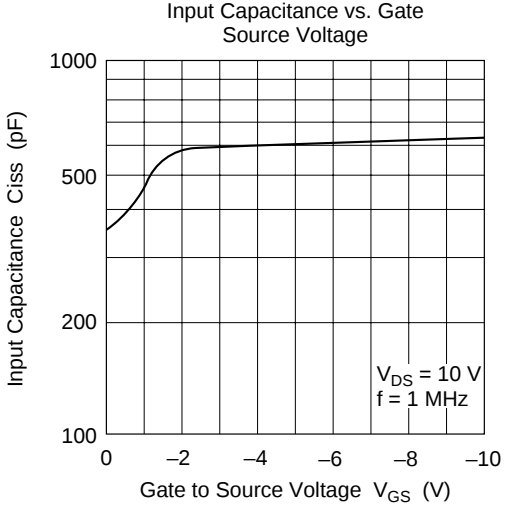
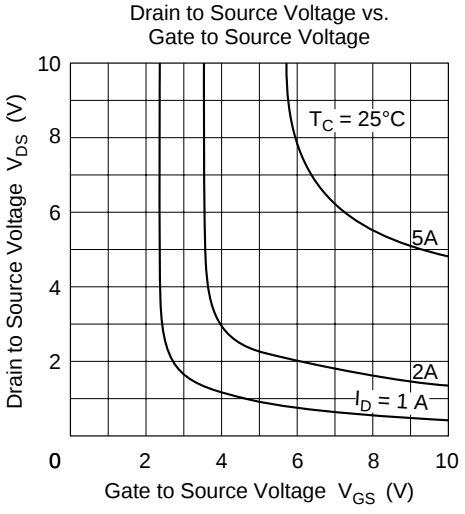
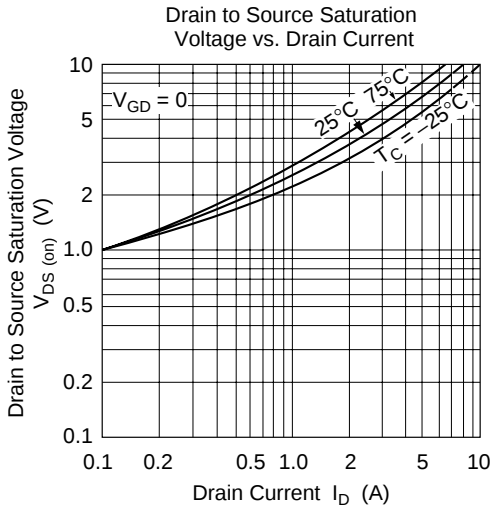
Note: 1. Value at Tc = 25°C

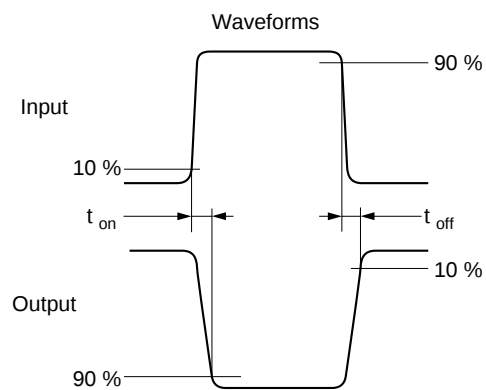
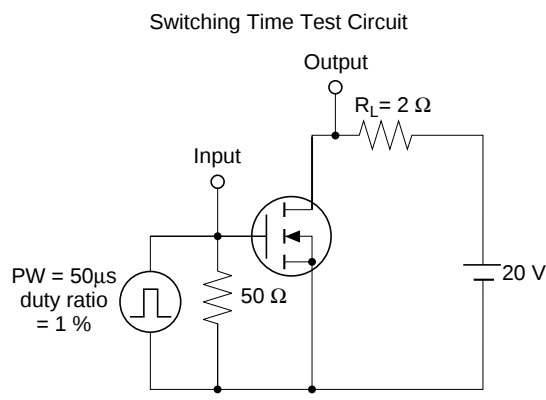
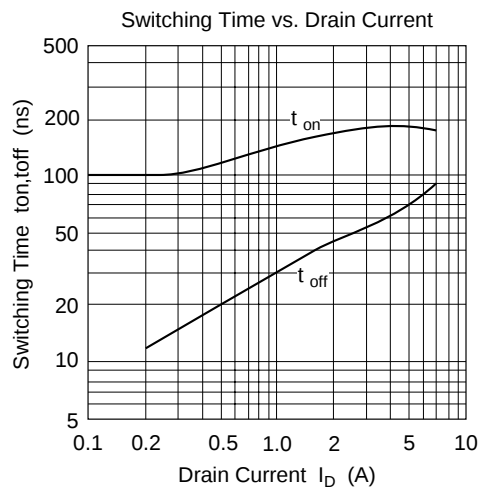
Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Item		Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	2SK1056 2SK1057 2SK1058	$V_{(BR)DSX}$	120 140 160	—	—	V	$I_D = 10\text{ mA}$, $V_{GS} = -10\text{ V}$
Gate to source breakdown voltage		$V_{(BR)GSS}$	± 15	—	—	V	$I_G = \pm 100\text{ }\mu\text{A}$, $V_{DS} = 0$
Gate to source cutoff voltage		$V_{GS(off)}$	0.15	—	1.45	V	$I_D = 100\text{ mA}$, $V_{DS} = 10\text{ V}$
Drain to source saturation voltage		$V_{DS(sat)}$	—	—	12	V	$I_D = 7\text{ A}$, $V_{GD} = 0$ *1
Forward transfer admittance		$ y_{fs} $	0.7	1.0	1.4	S	$I_D = 3\text{ A}$, $V_{DS} = 10\text{ V}$ *1
Input capacitance		C_{iss}	—	600	—	pF	$V_{GS} = -5\text{ V}$, $V_{DS} = 10\text{ V}$,
Output capacitance		C_{oss}	—	350	—	pF	$f = 1\text{ MHz}$
Reverse transfer capacitance		C_{rss}	—	10	—	pF	
Turn-on time		t_{on}	—	180	—	ns	$V_{DD} = 20\text{ V}$, $I_D = 4\text{ A}$,
Turn-off time		t_{off}	—	60	—	ns	

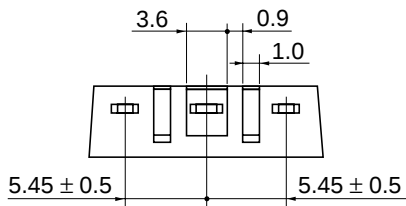
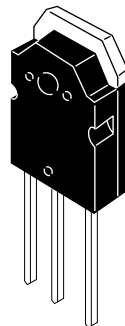
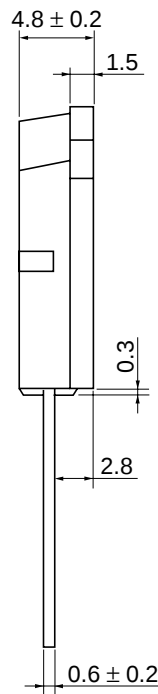
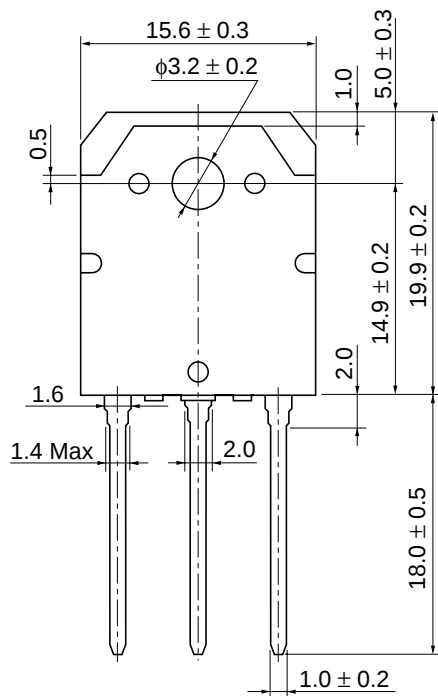
Note: 1. Pulse test







Unit: mm



Hitachi Code	TO-3P
JEDEC	—
EIAJ	Conforms
Weight (reference value)	5.0 g

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Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

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For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, San Jose, CA 95134 Tel: <1> (408) 433-1990 Fax: <1> (408) 433-0223	Hitachi Europe GmbH Electronic components Group Dornacher Straße 3 D-85622 Feldkirchen, Munich Germany Tel: <49> (89) 9 9180-0 Fax: <49> (89) 9 29 30 00 Hitachi Europe Ltd. Electronic Components Group. Whitebrook Park Lower Cookham Road Maidenhead Berkshire SL6 8YA, United Kingdom Tel: <44> (1628) 585000 Fax: <44> (1628) 778322
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Hitachi Asia Pte. Ltd. 16 Collyer Quay #20-00 Hitachi Tower Singapore 049318 Tel: 535-2100 Fax: 535-1533 Hitachi Asia Ltd. Taipei Branch Office 3F, Hung Kuo Building, No.167, Tun-Hwa North Road, Taipei (105) Tel: <886> (2) 2718-3666 Fax: <886> (2) 2718-8180
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Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX

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